MA114

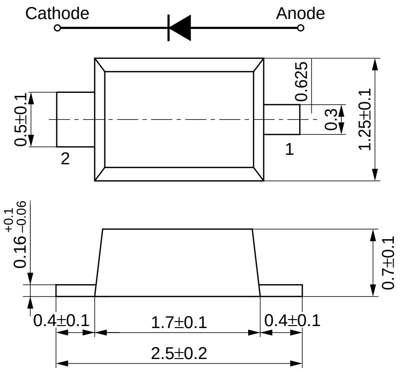
Silicon epitaxial planer type

For small power rectification

■ Features

- ● Small S-Mini type package enabling high density mounting
- ● High reverse voltage V_R

Unit : mm



1 : Anode
2 : Cathode
S-Mini Type Package (2-pin)

Marking Symbol : 1E

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	150	V
Peak reverse voltage	V_{RM}	150	V
Output current	I_O	200	mA
Non-repetitive peak forward surge current	I_{FSM} *	500	mA
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	– 55 to +150	˚C

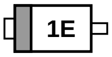
* t=1s

■ Electrical Characteristics (Ta= 25˚C)

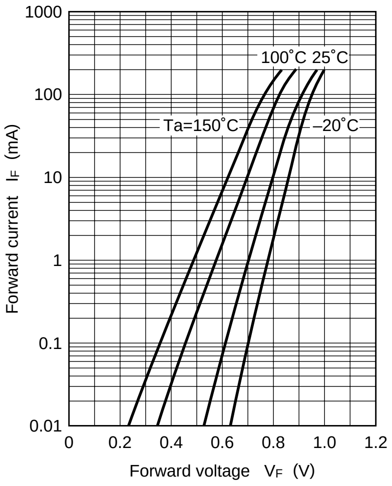
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R=150V			200	nA
Forward voltage (DC)	V_F	I_F= 200mA			1.2	V
Terminal capacitance	C_t	V_R= 0V, f=1MHz		4.5		pF

❖ Rated input/output frequency : 3MHz

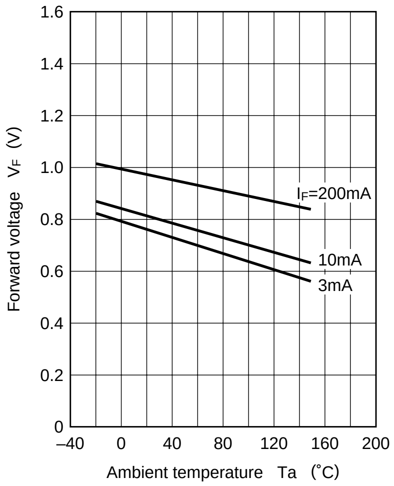
■ Marking



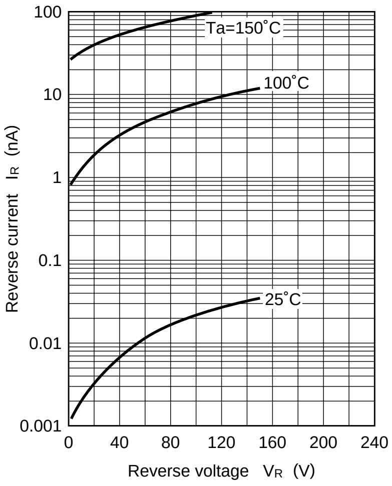
$I_F - V_F$



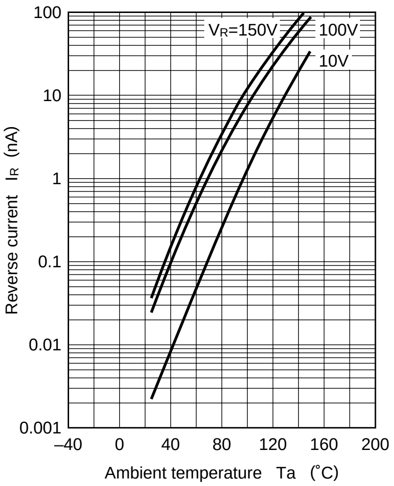
$V_F - Ta$



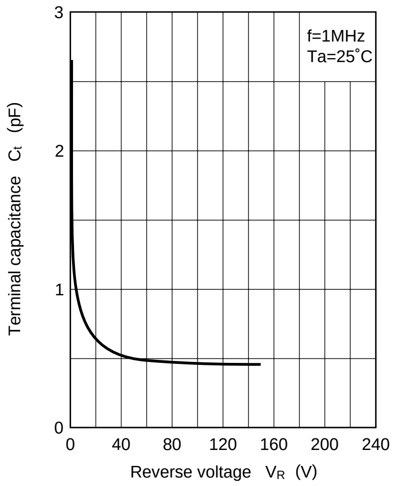
$I_R - V_R$



$I_R - Ta$



$C_t - V_R$



$I_{F\,(surge)} - t_W$